



SPN11T10 N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN11T10 is the N-Channel logic enhancement mode power field effect transistor which is produced using super high cell density DMOS trench technology. The SPN11T10 has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

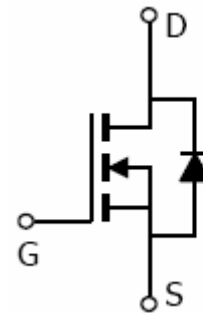
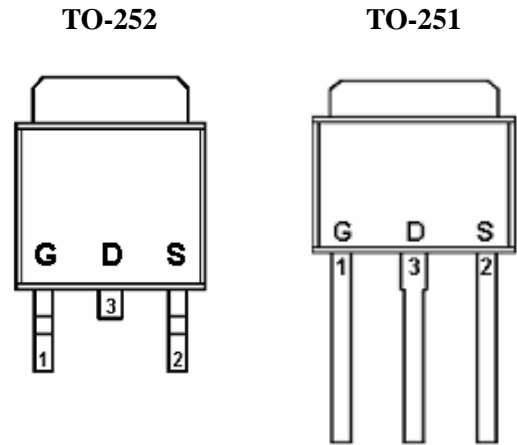
FEATURES

- ◆ 100V/8A, $R_{DS(ON)}=120m\Omega@V_{GS}=10V$
- ◆ High density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TO-252, TO-251 package design

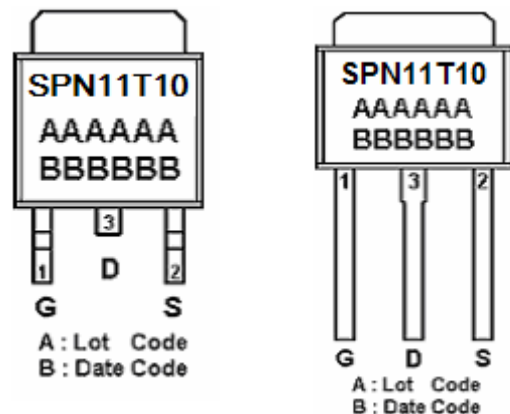
APPLICATIONS

- Powered System
- DC/DC Converter
- Load Switch

PIN CONFIGURATION



PART MARKING





SPN11T10

N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN11T10T252RGB	TO-252	SPN11T10
SPN11T10T251TGB	TO-251	SPN11T10

※ SPN11T10T252RGB : Tape Reel ; Pb – Free ; Halogen - Free

※ SPN11T10T251RGB : Tube ; Pb – Free ; Halogen - Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V _{DSS}	100	V	
Gate –Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	16	A
		TA=70°C	10.0	
Pulsed Drain Current	I _{DM}	50	A	
Avalanche Current	I _{AS}	14	A	
Power Dissipation @ TA=25°C	P _D	40	W	
Operating Junction Temperature	T _J	150	°C	
Storage Temperature Range	T _{STG}	-55/150	°C	
Thermal Resistance-Junction to Ambient	R _{θJA}	110	°C/W	



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ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1		3	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			25	uA
		$V_{DS}=80V, V_{GS}=0V$ $T_J=125^\circ C$			250	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\geq 5V, V_{GS}=10V$	11			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$			120	mΩ
		$V_{GS}=4.5V, I_D=3A$			200	mΩ
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=8A$		7.3		S
Diode Forward Voltage	V_{SD}	$I_S=8A, V_{GS}=0V$			1.3	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=80V, V_{GS}=10V$ $I_D=10A$		13	21	nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			6		
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V$ $f=1MHz$		450	720	pF
Output Capacitance	C_{oss}			65		
Reverse Transfer Capacitance	C_{rss}			50		
Turn-On Time	$t_{d(on)}$	$V_{DD}=50V, R_L=5\Omega$ $I_D=10A, V_{GEN}=10V$ $R_G=3.3\Omega$		5		nS
	t_r			17		
Turn-Off Time	$t_{d(off)}$			15		
	t_f			4.4		



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TYPICAL CHARACTERISTICS

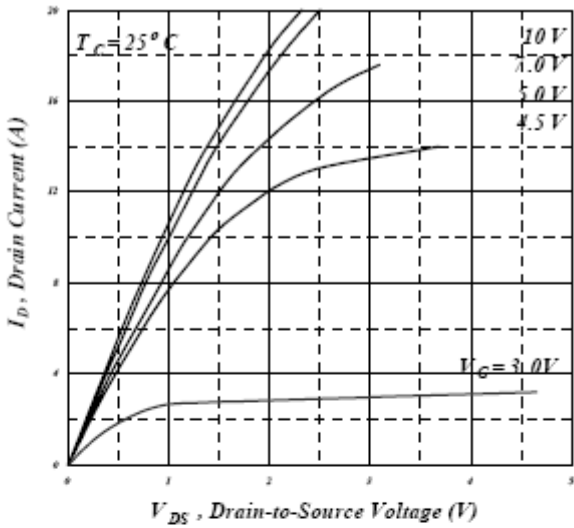


Fig 1. Typical Output Characteristics

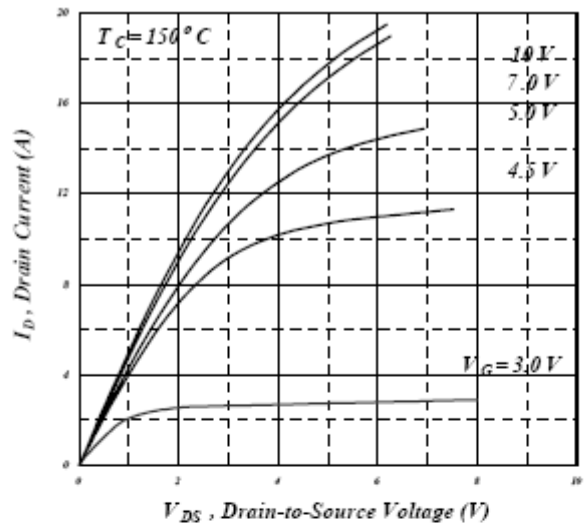


Fig 2. Typical Output Characteristics

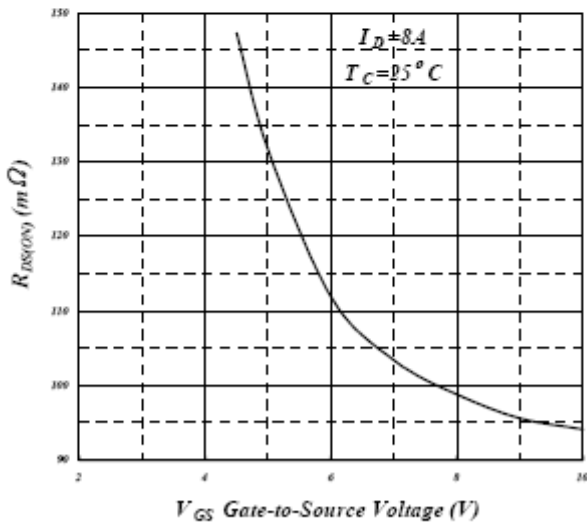


Fig 3. On-Resistance v.s. Gate Voltage

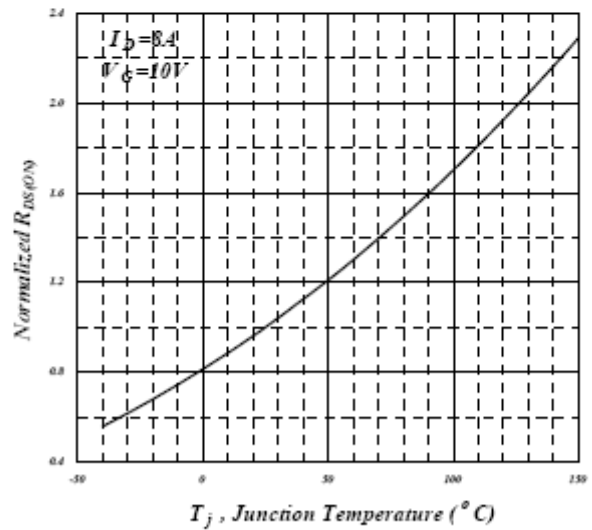


Fig 4. Normalized On-Resistance v.s. Junction Temperature



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TYPICAL CHARACTERISTICS

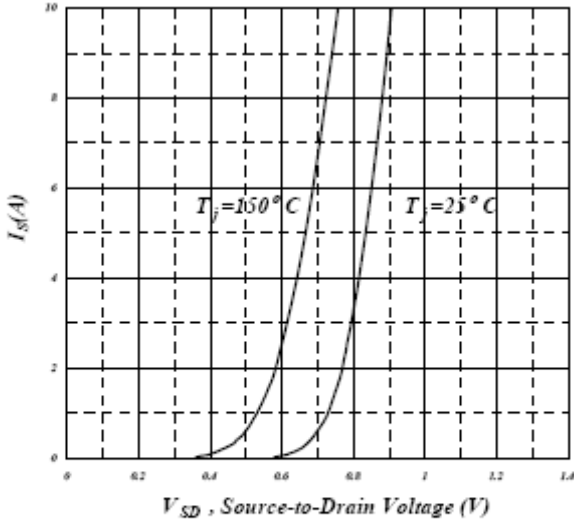


Fig 5. Forward Characteristic of Reverse Diode

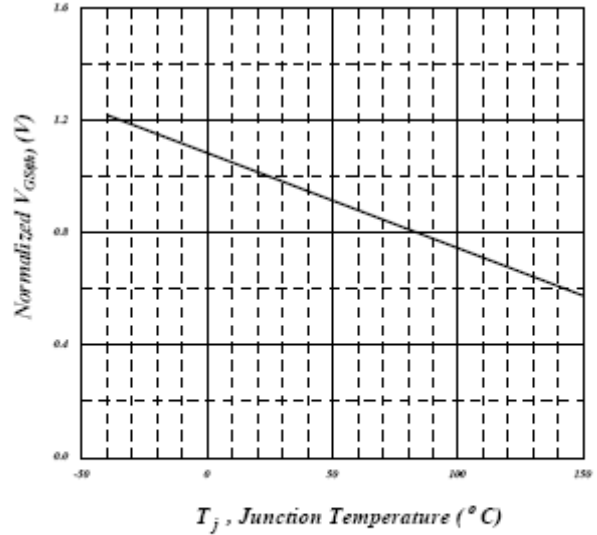


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

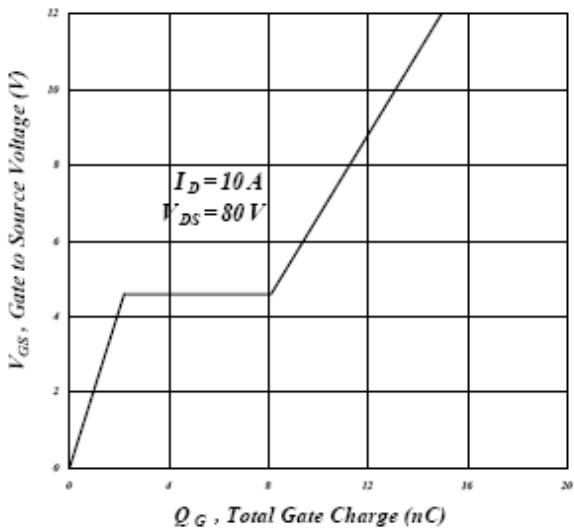


Fig 7. Gate Charge Characteristics

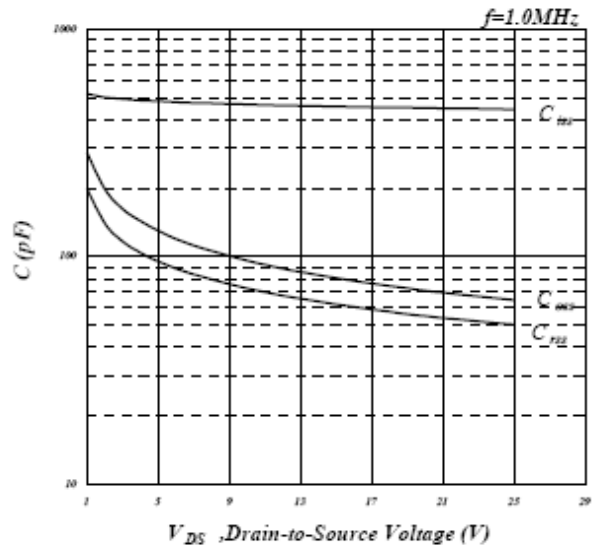


Fig 8. Typical Capacitance Characteristics



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TYPICAL CHARACTERISTICS

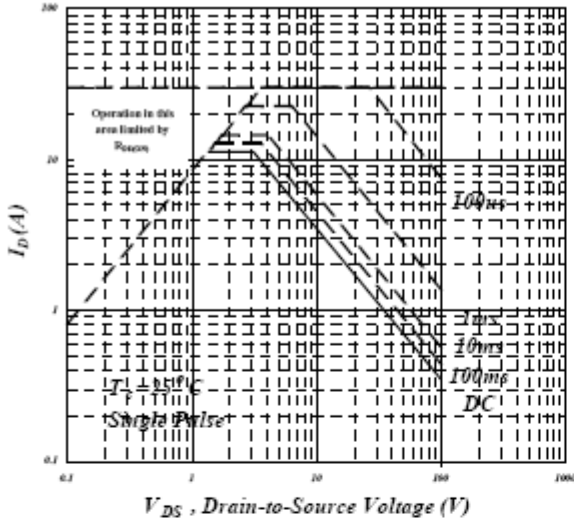


Fig 9. Maximum Safe Operating Area

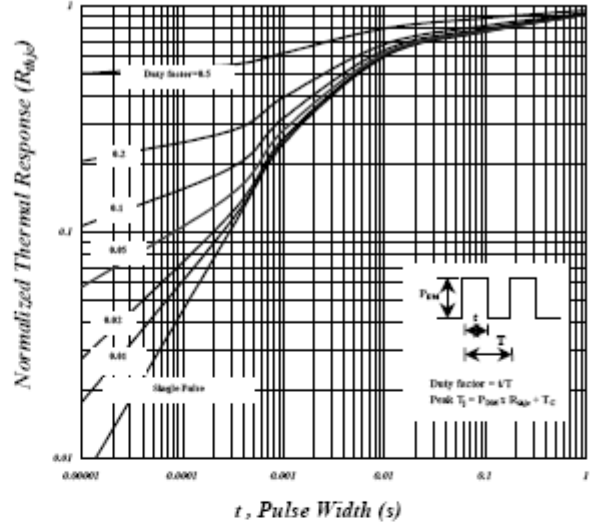


Fig 10. Effective Transient Thermal Impedance

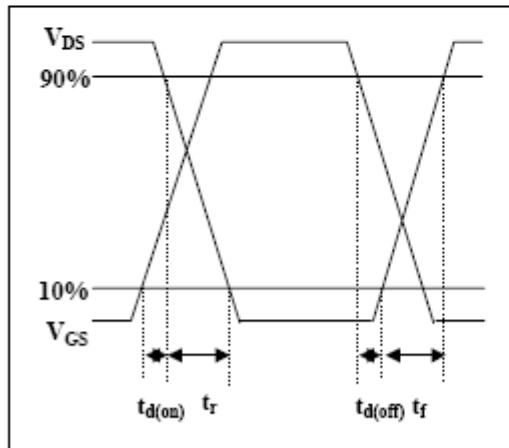


Fig 11. Switching Time Waveform

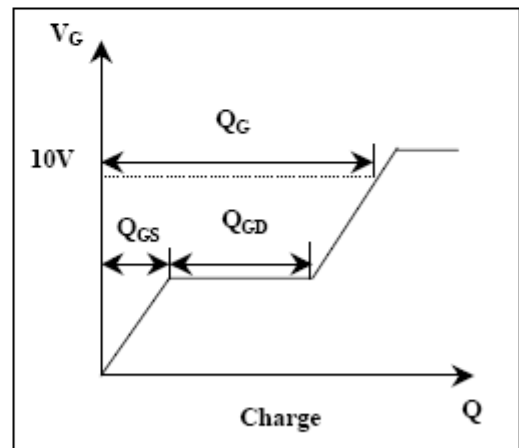


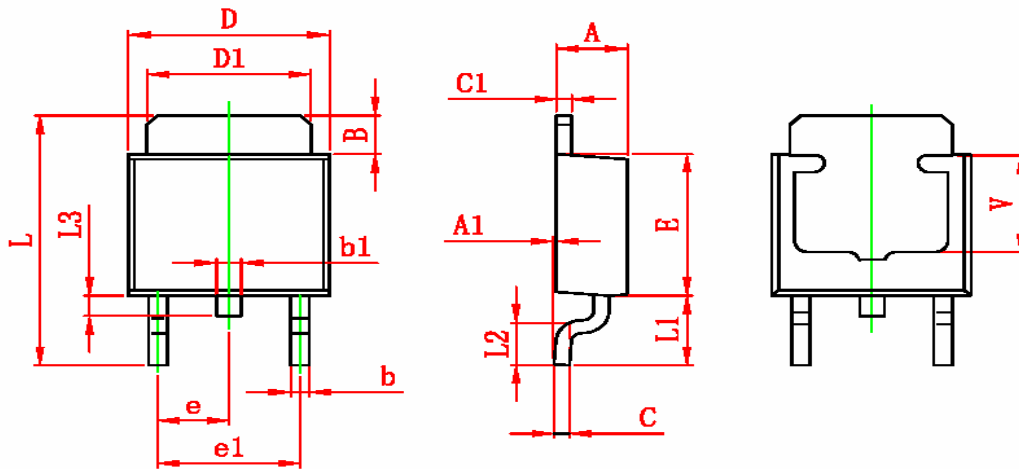
Fig 12. Gate Charge Waveform



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TO-252 PACKAGE OUTLINE



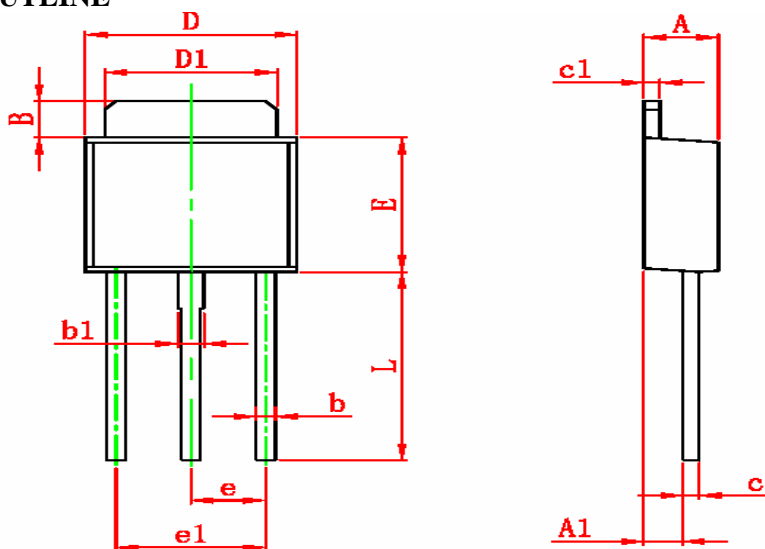
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.350	0.650	0.014	0.026
V	3.80 REF		0.150 REF	



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TO-251 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	1.020	1.270	0.040	0.050
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311



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